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MOLECULAR ELECTRONICS: Switching, Dynamics and Control

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These are preliminary lecture notes, intended only for distribution to participants.

TRANSPORT IN MOLECULAR JUNCTIONS

Trieste 2004

Outline:

SOME GENERALITIES LANDAUER AND KELDYSH PICTURES MOLECULAR ELECTRONICS CHALLENGES

ELECTRON TRANSFER AND ELECTRON CONDUCTANCE CHARGE BUILDUP AT JUNCTIONS - INTERFACES VOLTAGE ENGINEERING

MECHANISMS: INCOHERENCE TUNNELING TIMES DNA AND MECHANISMS DYNAMICS AND SWITCHING



Molecular Wire Junctions: Some Mechanisms and Transport Behaviors

•NEGF Formulation

•Simple Tunneling Transport

Incoherent Transport

Geometry Modulation

<u>Non – Ohmic transport</u>

Reed group, Break junction





Technically:

PW 91 DFT calculation Soft pseudopotentials Extended basis on molecule Optimized molecular geometry Non-equilibrium Green function for bulk

> default junction geometry truncated gold basis set



Standard Test Case (Reed, 1997) Benzenedithiol /Gold Break Junction





Biggish cluster, 3D Shows conductance fluctuations: g(atop)/g(FCC) = 2.4



SAMs on Au(111)-STM Images

Octanethiol





Octanethiol/Au(111)



Poirier, Chem. Rev. 97, 1117 (1997)





Arenethiol/Au(111) *Yang et al, J. Phys. Chem. B 104, 9059 (2000))*



Reproducibility ok in alkanethiols, poor in aromatics (Reed, 2003)

Dynamical conductance fluctuations How many molecules are required for switching? 1.



Mantooth, Donhauser, Kelly & Weiss Review of Scientific Instruments <u>73</u>, 313 (2002)

Conductance Fluctuations?

- multiple stable sites, low barriers
- conductance changes with site symmetry
- characteristic of Lewis bonding like Au/thiol

Thiol/Gold Interfaces??

- •Schottky barriers from charge flow
- •Fluid geometry from Lewis binding
- •Sigma/pi problems
- •Relatively poor spectral density
- •Facile and general structure formation

ALTERNATIVES?

BETTER LEWIS BINDING (ISOCYANIDE/Pt)
COVALENT BINDING AT SEMICONDUCTORS

Covalent attachment NDR



Molecule on *Clean Si(100)*

Hersam, NanoLetters 2004

Tunneling Time



Rate time $= k_{ET}^{-1} \approx 10^{-13} - 10^{-8} \text{ sec}$ <u>Tunneling time??</u>

Landauer Buttiker Time



Clock frequency = f At resonance, the ratio $\rightarrow / \rightarrow Maximizes, and$ $f = 2\pi / \tau_{LB}$

Landauer Buttiker Time



As B increases, LB time drops, Rate time increases How to generalize this to rate problems??

Model for tunnel time



t = 0: electron in $(0,)^{\dagger}$

 $\mathbf{R} = \mathbf{P}[\]/(\mathbf{P}[\] + \mathbf{P}[\])$

R can index tunneling time some complicated arithmetic suggests:

The equivalent of the Landauer/Buttiker time (for superexchange system)

NOTE:

tunnel time looks like uncertainty time tunnel time linear in N tunnel time independent of V

Landauer-Buttiker Contact Time For Wires

$$\tau_{\rm LB} = N\hbar/(gap)$$

So: big gaps, short wires (alkanes) give attosecond times, weak vibronic coupling, <u>Coherent ,T-independent tunneling transport</u>

Other times also enter

Wilkie, Nitzan, Jortner, MR

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•Geometry Modulation

Landauer-Buttiker Contact Time For Wires

$$\tau_{\rm LB} = N\hbar/(gap)$$

So: small gaps, long wires (aromatics) give times approaching nuclear motion suggesting nuclear coupling, dephasing, transition to activated motion

Other times also enter

Wilkie, Nitzan, Jortner, MRr

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I. Landauer Coherent Conductance

$$g = \frac{e^2}{h} \sum_{i} T_{ii}$$

 T_{ii} = transition probability in the ith transverse channel



Inelastic electron tunneling spectroscopy on SAMs







Wang et. al, NanoLetters (in press)

Hamiltonian for electrons and vibrations

$$\hat{H}_{0} = \sum_{k \in L, R} \varepsilon_{k}^{L, R} \hat{d}_{k}^{+} \hat{d}_{k}^{+} + \sum_{i, j} t_{ij} \hat{c}_{i}^{+} \hat{c}_{j}^{-} + \sum_{m} \omega_{m}^{bath} \hat{b}_{m}^{+} \hat{b}_{m}^{-} + \sum_{k} \omega_{k} \hat{a}_{k}^{+} \hat{a}_{k}^{-}$$

$$\stackrel{\text{leads}}{\underset{\text{electrons}}{}} \stackrel{\text{molecule}}{\underset{\text{electrons}}{}} \stackrel{\text{vibrons}}{\underset{\text{phonons}}{}} \stackrel{\text{phonons}}{\underset{\text{phonons}}{}}$$

Couplings and interactions are represented by the Hamiltonian

$$\begin{split} \hat{H}_{1} &= \sum_{k \in L, R; i} \left(V_{ki} \hat{d}_{k}^{+} \hat{c}_{i}^{-} + h.c. \right) + \sum_{i} V_{ij}^{ext} \hat{c}_{i}^{+} \hat{c}_{j}^{-} + \sum_{k, m} U_{m}^{k} \hat{A}_{k} \hat{B}_{m}^{-} + \sum_{k, i} M_{i}^{k} \hat{A}_{k} \hat{c}_{i}^{+} \hat{c}_{i}^{-} + \frac{1}{2} \sum_{i_{1}, i_{2}, i_{3}, i_{4}} V_{i_{3} i_{4}}^{i_{1} i_{2}} \hat{c}_{i_{1}}^{+} \hat{c}_{i_{2}}^{+} \hat{c}_{i_{4}} \hat{c}_{i_{3}}^{-} \hat{c}_{i_{4}}^{-} \hat{c}_{i_{3}}^{-} \hat{c}_{i_{4}}^{-} \hat{c}_{i_{3}}^{-} \hat{c}_{i_{4}}^{-} \hat{c}_{i_{3}}^{-} \hat{c}_{i_{4}}^{-} \hat{c}$$

Green function in composite system:

$$G(\tau,\tau') = G_0(\tau,\tau') + \int_c d\tau_1 \int_c d\tau_2 \ G_0(\tau,\tau_1) \Sigma(\tau_1,\tau_2) G(\tau_2,\tau')$$

$$\Sigma(\tau_1,\tau_2) = \Sigma^{ext} + \Sigma^L + \Sigma^R + \Sigma^{ph}$$

Electron/vibron coupling can be elastic or inelastic

Moving over and through the Injection Barrier



Expect to tunnel for short, cold junctions

hop for long, hot junctions

SYSTEM-BATH COUPLING -- CONGEPTS FROM NMR

$$\frac{1}{T_2} = \frac{1}{2T_1} + \frac{1}{T_2^*}$$

Longitudinal Relaxation









Multiple Oscillations

Density Matrix formalism

Used for systems with partial information

$$\rho_{ii} = populations$$

 $\rho_{ij} = coherences$

$$d\rho/dt = i[H, \rho] + d\rho/dt)_{diss}$$

<u>Time Dependence - Addd Vibronic</u> <u>Couplings, Dephasings</u>

$$\frac{d\rho_{ij}}{dt} = i \left[\rho, H\right] + \frac{d\rho_{ij}}{dt} \big|_{diss}$$

Bloch: $\frac{d\rho_{ij}}{dt} \big|_{diss} = \rho_{ij} \left(1 - \delta_{ij}\right) / T_2 + \delta_{ij} \rho_{ij} / T_1$

Damped oscillations \longrightarrow **rate processes**



It follow from the NMR example (using complicated theory that I would be delighted to discuss)

That there are **two mechanisms**

$$k = k_{coherent} + k_{incoherent}$$

$$k_{coherent} \approx \exp(-\beta r) \quad \leftarrow \text{For short and cold chains}$$

$$k_{incoherent} \approx 1/(a+br) \quad \leftarrow \text{For long and hot chains}$$





*in molecular systems



Carbon substrate

McCreery and Collaborators. Note :

Covalent bindingSemiconductor electrode

Carbon electrode junctions using Polyphenylenes show thermal turnover

Activation Energy Plot (All T)



McCreery et.al., 2003



Berlin Burin, MR



DFT (B3LYP, 6-31G**) geometry-optimized structures

Intramolecular rates do the same turnover in mechanism



Donor/ridge/acceptor photoexcited ET

Weiss, Wasielewski



Devices??

Molecular Switch?

Gate switching?



For effective gating, the gate oxide thickness Must be thinner than the source/drain length

This is tough with a short molecule!

Datta, Ghosh

A rectifier based on intra-molecular structural changes

(a device minimally dependent on the metal-molecule contact)



A SYSTEM WITH ONLY ONE THROUGH-SPACE COUPLING AND VERY HIGH ON/OFF CONDUCTANCE RATIO



Devices??

NANOCOMPOSITES IN TENNIS BALLS LOCK IN AIR, BUILD BETTER BOUNCE

Jan. 29, 2002 – When the first round of the Davis Cup gets under way Feb. 8, nanotechnology will be working, literally, within the game.





thanks

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- Emily Weiss
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- Bill Davis
- Alessandro Troisi
- Mike Wasielewski
- Vladi Mujica

ALL THE PARTICIPANTS!!



Multiple Charging steps!



<u>Molecular Wire Interconnects:</u> <u>Transport Regimes</u>



Rigorously: $g = g_{coherent} + g_{incoherent}$

 $g_{incoherent} \approx 1/(A + B * length)$ dissipation in electrodes, wire $g_{coherent} \approx exp(-\beta * length)$ dissipation in electrodes

ET-conductance relationship

$$k_{ET} = \frac{2\pi}{\hbar} T_{DA}^2 \rho_{FC}$$
$$g = \frac{2\pi e^2}{\hbar} T_{DA}^2 \rho_D \rho_A$$

Similar dependence of effective coupling on molecular parameters if Factorization electrode-wire holds.



<u>Table 1</u> Bridge length dependence of the transmission rate

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Physical Process	Bridge length (N) dependence	
Super exchange	e ^{-βN}	$\beta = 2\ln(V/\Delta E)$
(small N, large $\Delta E/V$, large $\Delta E/k_BT$)		
Steady state hopping	N^{-1}	
(large N, small $\Delta E/V$, small $\Delta E/k_BT$)		
Non-directional hopping	N^{-2}	
(large N, small $\Delta E/V$, small $\Delta E/k_BT$)		
Intermediate range	$\left(k_{up}^{-1} + k_{diff}^{-1}N\right)^{-1}$	$k_{up} \sim \left(V^2 \kappa / \Delta E^2 \right) e^{-\Delta E / k_B T}$
(intermediate N, small $\Delta E/V$)		$k_{diff} \sim \left(4V^2/\kappa\right)e^{-\Delta E/k_BT}$
		(Markovian case)
Steady state hopping + competing	$e^{-\alpha N}$	$\alpha = \sqrt{\Gamma_B \left(\Gamma_B + \kappa\right)} / 2V$
loss at every bridge site		(Markovian case)

Multiple Charging steps!





